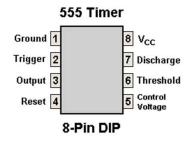
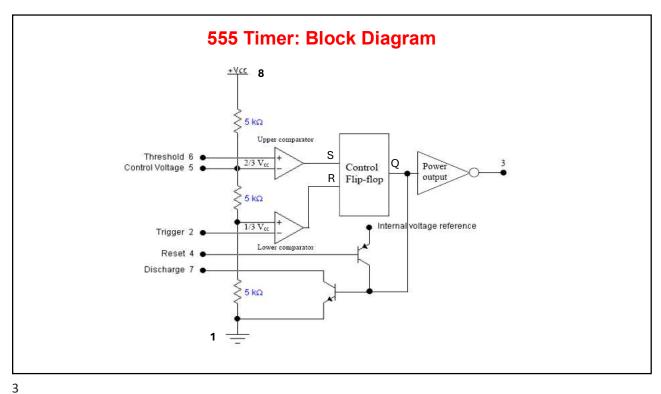
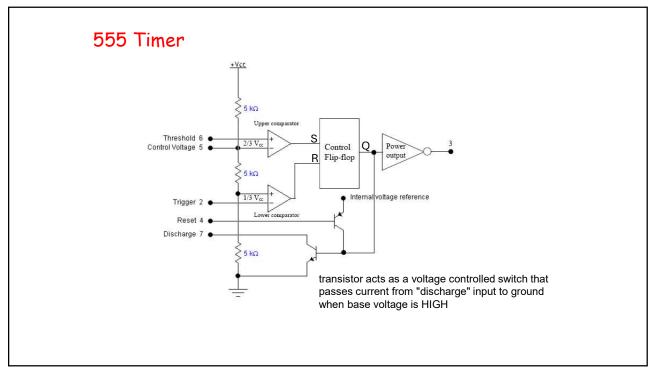


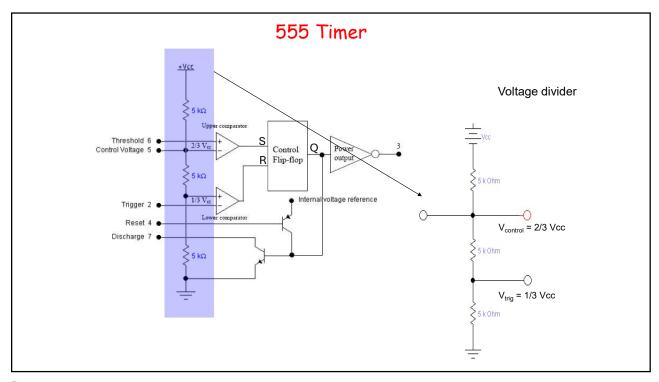
# 555 Timer IC

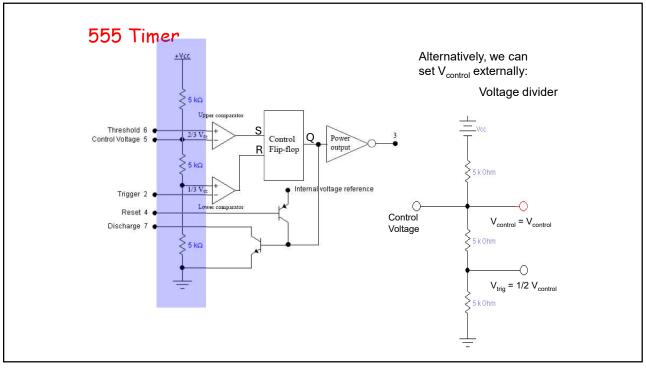
 $\bullet$  For lowish frequencies (<1MHz), a cheap and reliable clock can be made with a 555 timer chip.

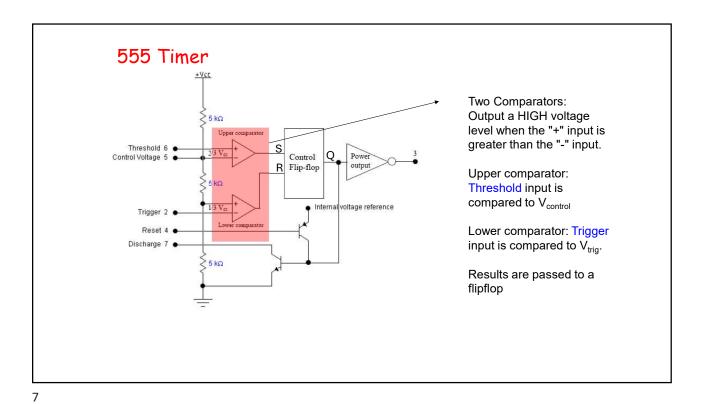


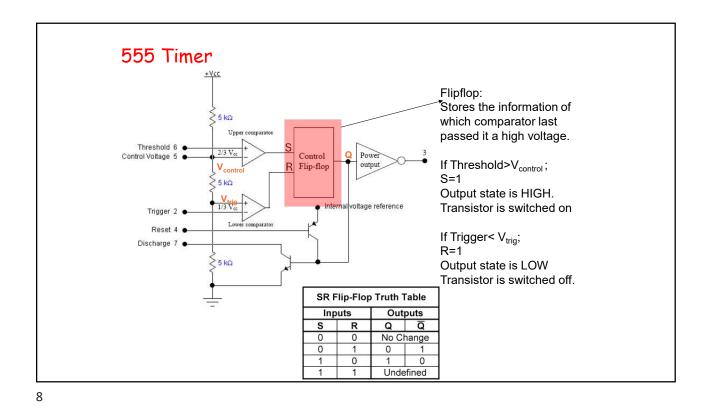


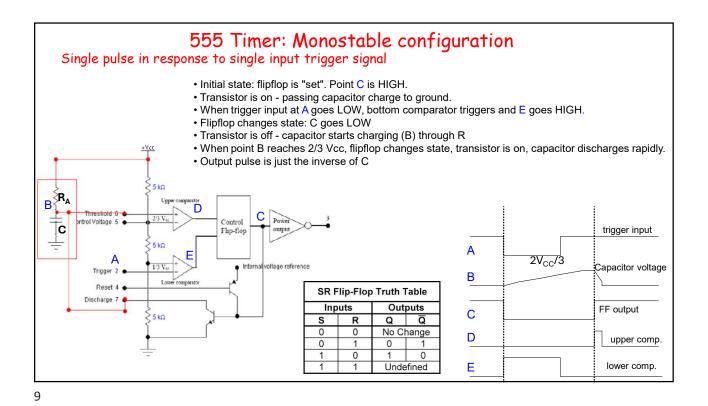




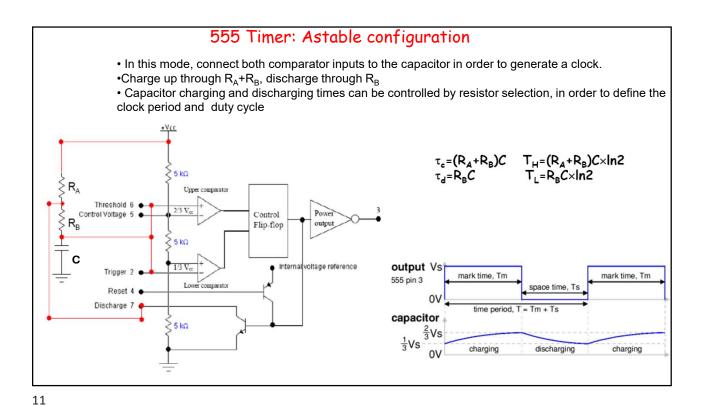








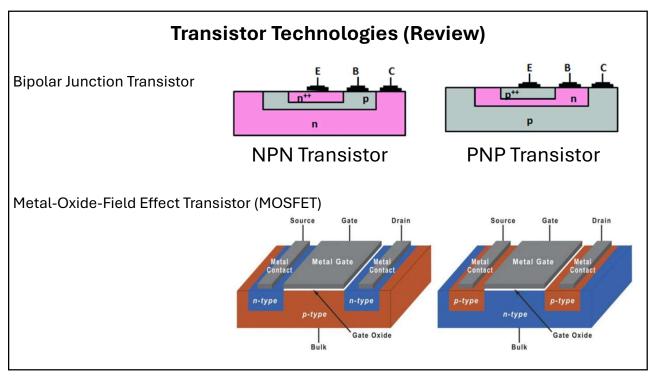
Time duration for which output remains High in Monostable Multivibrator / configuration:  $T_H$  = The Time Required to charge Capacitor C with Voltage  $v_c$  =  $2V_{CC}/3$ . Capacitor Charging Equation  $v_c = V_{CC}(1 - e^{-t/RC})$ +Vcc Trigger At  $v_c = 2V_{CC}/3$ 2/3Vcc pulses 1/3Vcc (pin 2) 0V C1 Charges C1 discharged  $t = R_A C \ln(3) = 1.0986 R_A C \approx 1.1 R_A C$ +Vcc via R1 via transistor 2/3Vcc Pins 6 & 7 1/3Vcc 0V \_ =1.1RC +Vcc Output (pin 3) 0V Unstable Stable The monostable circuit has only one stable state (output low). state state Monostable 555 operation

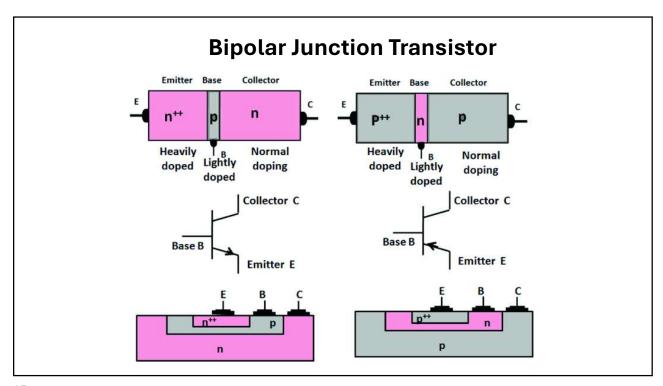


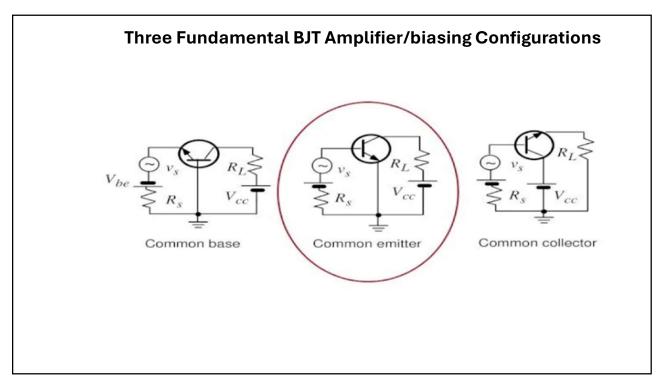
Time duration for which output remains High in Astable configuration:  $T_H$  = The Time Required to charge Capacitor C from  $V_{cc}/3$  to  $2V_{cc}/3$  trough  $R_A$  and  $R_B$ Gen. eq. of Capacitor Charging  $v_c = V_{CC}(1 - e^{-t/RC})$ Time required from 0 V to  $V_{cc}/3 = t_1$  $V_{cc}/3 = V_{CC}(1 - e^{-t}_1/(R_A + R_B)^C) => t_1 = (R_A + R_B)C*In(3/2)$ Time required from 0 V to 2Vcc/3=t<sub>2</sub>  $2*V_{cc}/3 = V_{CC}(1-e^{-t_2/(R_A+R_B)C}), => t_2 = (R_A+R_B)*C*In(3)$ Therefore, Time required to charge  $V_{cc}/3$  to  $2V_{cc}/3 = t_2 - t_1 = T_H = (R_A + R_B)^*C^*ln(2) = 0.693 (R_A + R_B)^*C$ Time duration for which output remains LOW in Astable configuration: Similarly, the discharging equation from 2Vcc/3 at any instant t, is given by v<sub>c</sub>=2vcc/3 \*e<sup>-t/R</sup><sub>B</sub><sup>C</sup> If Time of discharging from 2Vcc/3 to  $Vcc/3 = T_L$  $Vcc/3=2V_{CC}/3 *e^{-T_{L}/R_{B}C}$  =>  $T_{L}=R_{B}C*ln(2)=0.693 R_{B}C$ V<sub>s</sub>=V<sub>cc</sub> Overall, period of the square wave T= T<sub>H</sub>+ T<sub>I</sub> = 0.693(R<sub>A</sub>+2R<sub>B</sub>)C output Vs mark time, Tm mark time, Tm 555 pin 3 0 Duty cycle= $T_H/(T_H+T_L)=(R_B+R_A)/(2R_B+R_A)$ time period, T = Tm + Ts capacitor charging discharging charging 0V

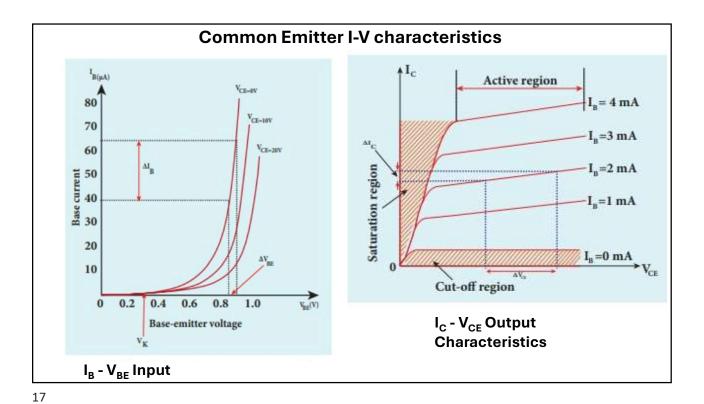
# **Basics of Transistors**

13







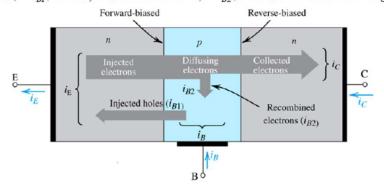


Physical structure of bipolar junction transistor (BJT) ☐ Both electrons and holes participate in the conduction process for bipolar devices □ BJT consists of two pn junctions constructed in a special way and connected in series, back to back ☐ The transistor is a three-terminal device with emitter, base and collector terminals ☐ From the physical structure, BJTs can be divided into two groups: npn and pnp transistors Metal contact contact n-type p-type n-type p Collector Emitter Base Eo Emitter Base Collector Collector region region region (C) Emitter-base Collector-base (EBJ) (CBJ) Modes of operation ☐ The two junctions of BJT can be either forward or reverse-biased Mode EBJ CBJ ☐ The BJT can operate in different modes depending on the junction bias Cutoff Reverse Reverse ☐ The BJT operates in active mode for amplifier circuits Active Forward Reverse ☐ Switching applications utilize both the cutoff and saturation modes Saturation Forward Forward

#### Operation of the npn transistor in the active mode

☐ Terminal currents of BJT in active mode:

$$\begin{split} &i_{\rm E}({\rm emitter\; current}) = i_{\rm En}({\rm electron\; injection\; from\; E\; to\; B}) + i_{\rm Ep}({\rm hole\; injection\; from\; B\; to\; E}) \\ &i_{\rm C}({\rm collector\; current}) = i_{\rm Cn}({\rm electron\; drift}) + i_{\rm CBO}({\rm CBJ\; reverse\; saturation\; current\; with\; emitter\; open}) \\ &i_{\rm B}({\rm base\; current}) = i_{\rm Bi}({\rm hole\; injection\; from\; B\; to\; E}) + i_{\rm Bi}({\rm recombination\; in\; base\; region}) \end{split}$$

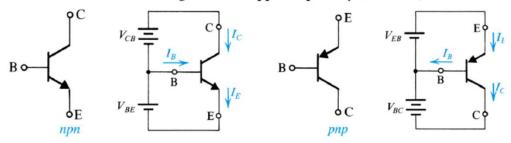


19

### Circuit symbols, voltage polarities and current flow

☐ Terminal currents are defined in the direction as current flow in active mode

☐ Negative values of current or voltage mean in opposite polarity (direction)

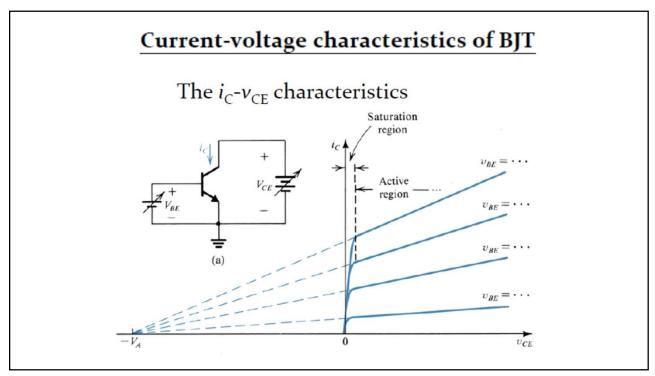


#### Summary of the BJT current-voltage relationships in the active mode

- ☐ The terminal currents for a BJT in active mode solely depend on the junction voltage of EBJ
- ☐ The ratios of the terminal currents for a BJT in active mode are constant
- $\Box$  The current directions for npn and pnp transistors are opposite

npn transistor	pnp transistor	
$i_{C} = I_{S}e^{v_{BE}/V_{T}}$ $i_{B} = \frac{i_{C}}{\beta} = \frac{I_{S}}{\beta}e^{v_{BE}/V_{T}}$ $i_{E} = \frac{i_{C}}{\alpha} = \frac{I_{S}}{\alpha}e^{v_{BE}/V_{T}}$	<i>P P</i>	$i_{E} = i_{C} + i_{B}$ $\alpha = \frac{\beta}{\beta + 1}$ $\beta = \frac{\alpha}{1 - \alpha}$

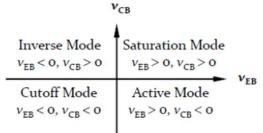
21



#### BJT operation modes

- ☐ The BJT operation mode depends on the voltages at EBJ and BCJ
- ☐ The I-V characteristics are strongly nonlinear
- ☐ Simplified models and classifications are needed to speed up the hand-calculation analysis

# npn transistor $\nu_{\rm BC}$



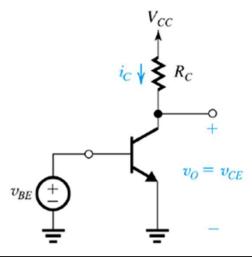
pnp transistor

Applications: as a switch and as an Amplifier

23

# BJT voltage amplifier

- $\square$ A BJT circuit with a collector resistor  $R_{\mathbb{C}}$  can be used as a simple voltage amplifier
- ☐ Base terminal is used the amplifier input and the collector is considered the amplifier output
- $\Box$  The voltage transfer characteristic (VTC) is obtained by solving the circuit from low to high  $v_{BE}$





# **Voltage Transfer Characteristics**

↑ Cut off → Active ← Saturation

 $\rightarrow$  o V  $\leq$   $v_{BE}$  < 0.5 V and  $i_{C}$  = 0

 $\rightarrow v_{\rm O} = v_{\rm CE} = V_{\rm CC}$ 

■ Active mode:

 $\rightarrow v_{BE} > 0.5 \text{ V} \text{ and } i_{C} = I_{S} \exp(v_{BE}/V_{T})$ 

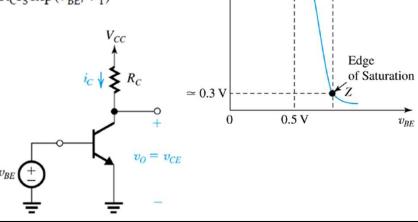
 $\rightarrow v_{\text{O}} = V_{\text{CC}} - i_{\text{C}}R_{\text{C}} = V_{\text{CC}} - R_{\text{C}}I_{\text{S}}\exp(v_{\text{BE}}/V_{\text{T}})$ 

■ Saturation:

 $\rightarrow v_{\rm BE}$  further increases

 $\rightarrow v_{CE} = v_{CEsat} = 0.2 \text{ V}$ 

 $\rightarrow v_0 = 0.2 \text{ V}$ 



25

**Thanks**